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**BIELE-013** 

## B.Tech. - VIEP - ELECTRONICS AND COMMUNICATION ENGINEERING (BTECVI).

## **Term-End Examination**

00319

December, 2017

## BIELE-013 : DEVICE MODELLING FOR CIRCUIT SIMULATION

Time: 3 hours

Maximum Marks: 70

**Note:** Attempt any **seven** questions. All questions carry equal marks. Missing data may be suitably assumed. Use of scientific calculator is permitted.

1. Answer the following briefly:

*5*×2=*10* 

- (a) Mention the principle of circuit simulation and its objectives.
- (b) Define SPICE. How is it different from the verilog netlist of an analog circuit?
- (c) What is the difference between device modelling and device simulation?
- (d) What is body effect in MOSFET?
- (e) What is base width modulation of BJT?

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2.	(a)	Write a program using SPICE code in order		
		to simulate a half wave rectifier circuit.		
		Draw its input and output waveforms.	5	
	(b)	Mention the SPICE commands for AC, DC,		
		transient, noise and temperature analysis		
		of any analog circuit.	5	
3.	(a)	How is depletion region formed in a		
		p-n junction diode? Derive the expression		
		of depletion region width with respect to		
		junction built-in potential.	5	
	(b)	How are different model parameters of a		
		diode measured?	5	
4.	Draw	and explain various capacitances present in		
	MOS	FET. Also explain charge sharing effect in		
	MOS	FET.	10	
5.	(a)	Describe the static model of the ideal diode		
		and its implementation in SPICE.	5	
	(b)	Draw and explain the small signal model of		
		a p-n junction diode.	5	
6.	Desci	ribe high frequency and noise models of a		
	bipol	ar junction transistor.	10	
7.	Discu	ass the modelling of JFET and MESFET.	10	
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8.	(a)	What is meant by scaling of MOSFET?  What are the types of scaling? Explain any one scaling technique.  5
	(b)	What is channel length modulation and how does it affect the drain current of MOSFET?
9.	(a)	Draw the small signal model of MOSFET and mention the SPICE parameters with their values and units.
	(b)	Explain Level-1 and Level-2 large signal MOSFET models and write their advantages and disadvantages.
10.	Write follow	•
	(a)	Heterojunction Devices
	(b)	BSIM Model
	(c)	DIBL Effect